FUJITSU GENERAL ELECTRONICS LIMITED

FGI-6I050E065D1

IGBT MODULE 650V/50A IPM

■ Features

- · DC input, 3-phase AC output IGBT IPM
- Built -in various protection functions (Over current protection, Over heating protection, Under voltage protection)
- Short -circuit warranty type IGBT (5µs/125°C)
- · Reliability improvement by epoxy resin encapsulation



Dimensions

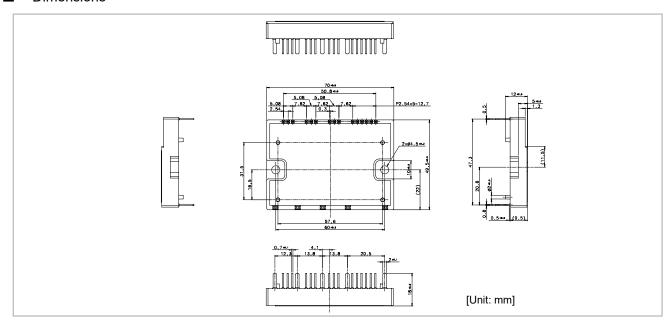


Fig.1. Dimensions

Pin Functions

Pin No.	Name	Function	Pin No.	Name	Function
1	GND U	Ground terminal (U)	9	Vcc W	Power supply (W)
2	Vin U	Driver input (U)	10	GND	Ground terminal (Under arm)
3	Vcc U	Power supply (U)	11	Vcc	Power supply for Under arm
4	GND V	Ground terminal (V)	12	Vin X	Driver input (X)
5	Vin V	Driver input (V)	13	Vin Y	Driver input (Y)
6	Vcc V	Power supply (V)	14	Vin Z	Driver input (Z)
7	GND W	Ground terminal (W)	15	ALM	Alarm output
8	Vin W	Driver input (W)			

■ Block Diagram

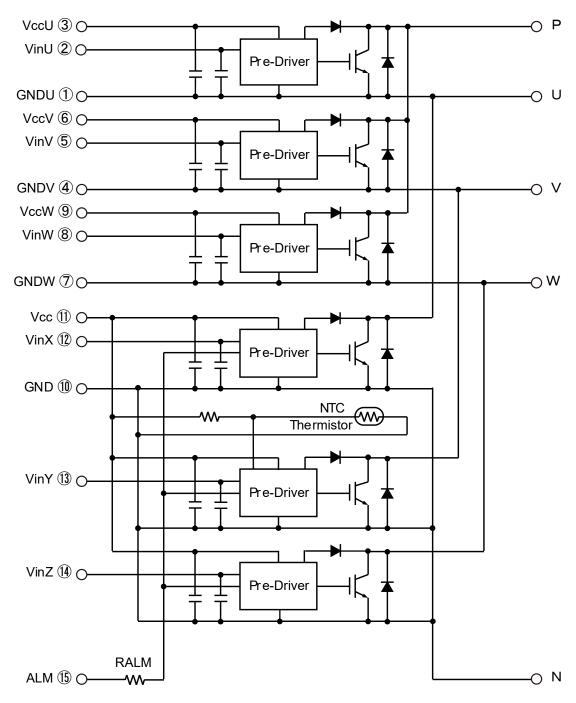


Fig.2. Block Diagram

■ Absolute Maximum Ratings (Tc=25°C, Vcc=15V unless otherwise specified)

Items			Min.	Max.	Units
Collector-Emitter Voltage (*1)		Vces	0	650	V
Short Circuit Voltage		Vsc	200	400	V
	DC	lc	ı	50	Α
Collector Current	1ms	Icp	-	100	Α
	Duty=100%(*2)	-lc	•	50	Α
Collector Power Dissipation	1 device (*3)	Pc	•	131	W
Supply Voltage of Pre-Driver (*4)	Vcc	-0.3	20	V	
Input Signal Voltage (*5)		Vin	-0.3	Vcc+0.5	V
Alarm Signal Voltage (*6)		V _{ALM}	-0.3	Vcc	V
Alarm Signal Current (*7)		I _{ALM}	•	20	mA
Junction Temperature		Tj	-	150	°C
Operating Case Temperature		Topr	-20	110	°C
Storage Temperature		Tstg	-40	125	°C
Solder Temperature (*8)		Tsol	•	260	°C
Isolating Voltage (*9)	Viso	1	AC2500	Vrms	
Screw Torque	Mounting (M4)	-	-	1.7	Ν·m

Note*1: Vces shall be applied to the input voltage between terminal P-(U,V,W) and (U,V, W)-N.

Note*4: Vcc shall be applied to the input voltage between terminal No.3 and 1, 6 and 4, 9 and 7, 11 and 10.

■ Electrical Characteristics (Tj=25°C Vcc=15V unless otherwise specified)

Items	Symbol	Conditions		Min.	Тур.	Max.	Units
Collector Current at off signal		Vce=650V		-	-	1.0	mA
Collector-Emitter saturation		Ic=50A	Terminal	-	-	2.28	V
Collector-Emitter Saturation	V _{CE(sat)}	IC-SUA	Chip	-	1.65	•	V
Forward voltage of FWD		I⊧=50A	Terminal	-	-	2.07	V
- Orward Voltage of 1 VVD	VF	IF=50A	Chip	-	1.45	-	V
	ton	V _{DC} =300V, T _i =125°C, I _C =50A		1.1	-	-	μs
Switching time	toff	VDC-300V, 1]-123 C), IC-30A	-	-	2.1	μs
	trr	V _{DC} =300V, I _F =50A		-	-	0.3	μs
Supply current of P-slde pre-drlver (per one unit)	Ісср	Switching Frequency=0-15kHz		-	-	13	mA
Supply current of N-side pre-driver	Iccn	Tc=-20~110°C		-	-	38	mA
Input signal threshold voltage	$V_{inth(on)}$	Vin-GND	ON	1.2	1.5	1.6	V
Input signal tilleshold voltage	V _{inth(off)}	OFF		1.5	1.65	1.9	V
Over Current Protection Level	loc	T _j =125°C		75	-	-	Α
Over Current Protection Delay time	tdoc	T _j =125°C		-	1.5	-	μs
Short Circuit Protection Delay time	t sc	T _j =125°C		-	3.7	5	μs
Over Heating Protection Temperature Level	Тон	Module center		140	•	•	Ŝ
Over Heating Protection Hysteresis	Тн			-	20	•	Ŝ
Under Voltage Protection Level	Vuv			11.0	-	12.5	V
Under Voltage Protection Hysteresis	Vн			0.2	0.5	-	V
	t _{ALM(OC)}	-ALM-GND -Tc=-20~110°C		1.0	1.3	(1.6)	ms
Alarm Signal Hold Time	t _{ALM(UV)}		Vcc≧10V	2.5	2.9	(3.2)	ms
	t _{ALM(Тон)}	1020-110 0		5.0	5.6	(6.2)	ms
Resistance for current limit	RALM			1170	1300	1430	Ω

Figures in () are reference values.

Note*2: Duty=125°C/Rth(j-c)D /(If×Vf Max.)×100

Note*3: Pc=125°C/Rth(j-c)Q

Note*5: Vin shall be applied to the input voltage between terminal No.2 and 1, 5 and 4, 8 and 7, 12 - 14 and 10.

Note*6: Valm shall be applied to the voltage between terminal No.15 and 10.

Note*7: IALM shall be applied to the input current to terminal No.15.

Note*8: Immersion time 10 ± 1sec.1time.

Note*9: Terminal to base, 50/60Hz sine wave 1min. All terminals should be connected together during the test.

■ Thermal Characteristics (Tc= 25°C)

Items			Symbol	Min.	Тур.	Max.	Units
Junction to Cook Thormal Beginlanes (*)	Inventor	IGBT	R _{th(j-c)Q}	-	-	0.95	°C/W
Junction to Case Thermal Resislance (*)	inverter	FWD I	R _{th(j-c)D}	-	-	1.12	°C/W
Case to Fin Thermal Resistance with Compound			R _{th(c-f)}	-	0.10	-	°C/W

Note *: For 1 device, the measurement point of the case is just under the chip.

■ Recommended Operating Conditions

Items	Symbol	Min.	Тур.	Max.	Units
DC Bus Voltage	V _{DC}	•	-	400	V
Power Supply Voltage of Pre-Driver	Vcc	13.5	15.0	16.5	V
Switching frequency of IPM		-	-	20	kHz
Arm shoot through blocking time for IPM's Input signal		1.0	-	-	μs
Screw Torque (M4)		1.3	-	1.7	N·m

■ Weight

Items	Symbol	Min.	Тур.	Max.	Units
Weight	Wt	-	80	-	g

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